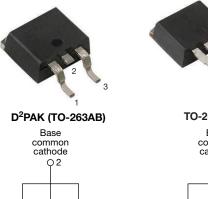
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# VS-20CTH03SHM3, VS-20CTH03-1HM3

### **Vishay Semiconductors**

### Hyperfast Rectifier, 2 x 10 A FRED Pt<sup>®</sup>



**d** 2 1 O Common O 3 Anode

**TO-262AA** Base common cathode 02 <u>d</u> 2 1 O Common O 3 Anode cathode Anode

VS-20CTH03-1HM3

Anode cathode VS-20CTH03SHM3

### LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub>	2 x 10 A					
V <sub>R</sub>	300 V					
V <sub>F</sub> at I <sub>F</sub>	0.85 V					
t <sub>rr</sub> typ.	23 ns					
T <sub>J</sub> max.	175 °C					
Package	D <sup>2</sup> PAK (TO-263AB), TO-262AA					
Circuit configuration	Common cathode					

#### **FEATURES**

- Hyperfast recovery time
- · Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 gualified, meets JESD 201, class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **DESCRIPTION / APPLICATIONS**

Vishay Semiconductors 300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

#### **MECHANICAL DATA**

Case: D<sup>2</sup>PAK (TO-263AB), TO-262AA Molding compound meets UL 94 V-0 flammability rating Terminal: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Peak repetitive reverse voltage		V <sub>RRM</sub>		300	V			
Average rectified forward current	per diode	I <sub>F(AV)</sub>	T <sub>C</sub> = 160 °C	10				
Average rectilied forward current	per device			20	А			
Non-repetitive peak surge current		I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	120				
Operating junction and storage ter	nperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C			

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	TEST CONDITIONS MIN.					
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	300	-	-	N		
	V <sub>F</sub>	I <sub>F</sub> = 10 A	-	1.05	1.25	V		
Forward voltage		I <sub>F</sub> = 10 A, T <sub>J</sub> = 125 °C	-	0.85	0.95			
Reverse leakage current		$V_R = V_R$ rated	-	-	20			
neverse leakage current	I <sub>R</sub>	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	6	200	μA		
Junction capacitance	CT	V <sub>R</sub> = 300 V	-	30	-	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8	-	nH		

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### **Vishay Semiconductors**

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_C = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	TEST CONDITIONS			MAX.	UNITS
		I <sub>F</sub> = 1.0 A, dI <sub>F</sub> /dt =	100 A/ $\mu$ s, V <sub>R</sub> = 30 V	-	23	-	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	31	-	ns
		T <sub>J</sub> = 125 °C		-	42	-	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 10 A dI <sub>F</sub> /dt = 200 A/μs V <sub>B</sub> = 200 V	-	2.4	-	A
Feak recovery current		T <sub>J</sub> = 125 °C		-	5.6	-	
	0	T <sub>J</sub> = 25 °C	•R - 200 V	-	36	-	nC
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	120	-	ne

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C		
Thermal resistance, junction to case per diode	R <sub>thJC</sub>		-	-	1.5	°C/W		
Thermal resistance, junction to ambient	R <sub>thJA</sub>		-	-	70	°C/W		
Maight			-	2.0	-	g		
Weight			-	0.07	-	oz.		
Madine device		Case style D <sup>2</sup> PAK (TO-263AB)	20CTH03SH					
Marking device		Case style TO-262AA	20CTH03-1H					

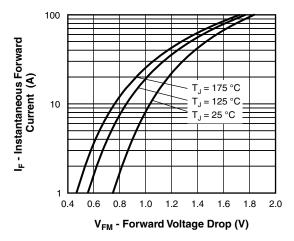


Fig. 1 - Maximum Forward Voltage Drop Characteristics

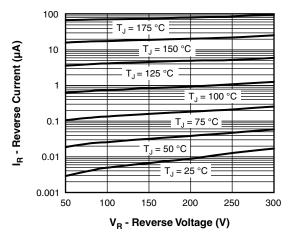


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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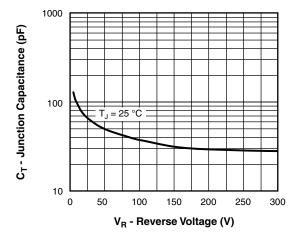


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

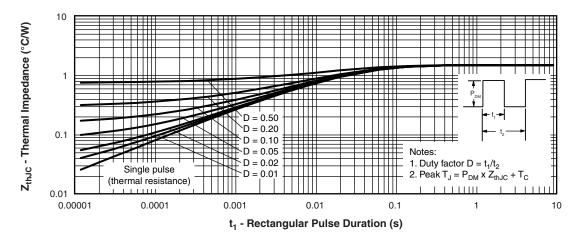
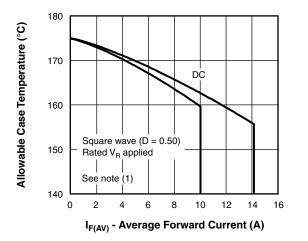
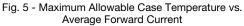


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics





#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$ 

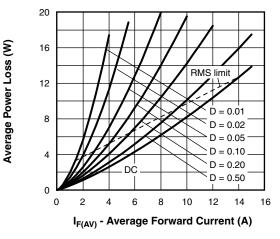


Fig. 6 - Forward Power Loss Characteristics

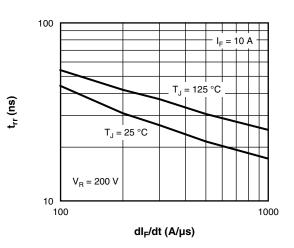
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Fig. 7 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

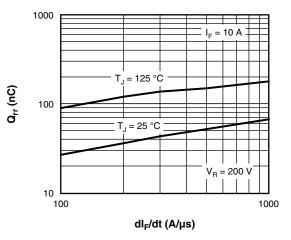


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

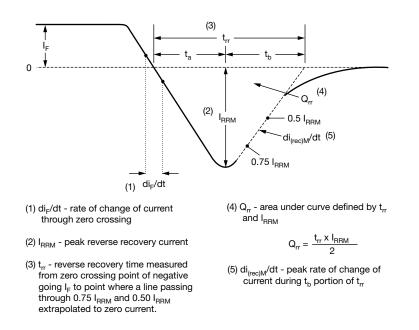
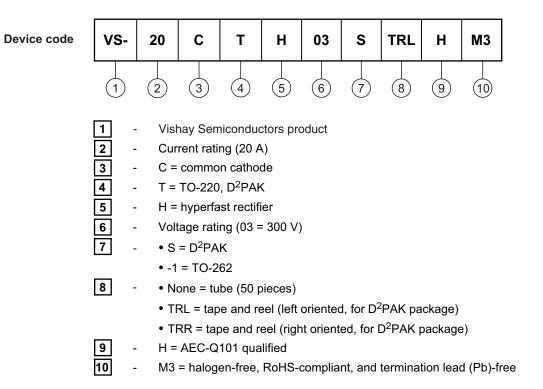


Fig. 9 - Reverse Recovery Waveform and Definitions



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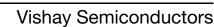
#### **ORDERING INFORMATION TABLE**



ORDERING INFORMATION (Example)						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-20CTH03SHM3	50	Antistatic plastic tubes				
VS-20CTH03STRLHM3	800	13" diameter plastic tape and reel				
VS-20CTH03STRRHM3	800	13" diameter plastic tape and reel				
VS-20CTH03-1HM3	50	Antistatic plastic tubes				

LINKS TO RELATED DOCUMENTS							
Dimensions	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?95046					
	TO-262AA	www.vishay.com/doc?95419					
Deut menduine information	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?95444					
Part marking information	TO-262AA	www.vishay.com/doc?95443					
Packaging information	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?95032					
SPICE model	·	www.vishay.com/doc?96583					

## **Outline Dimensions**

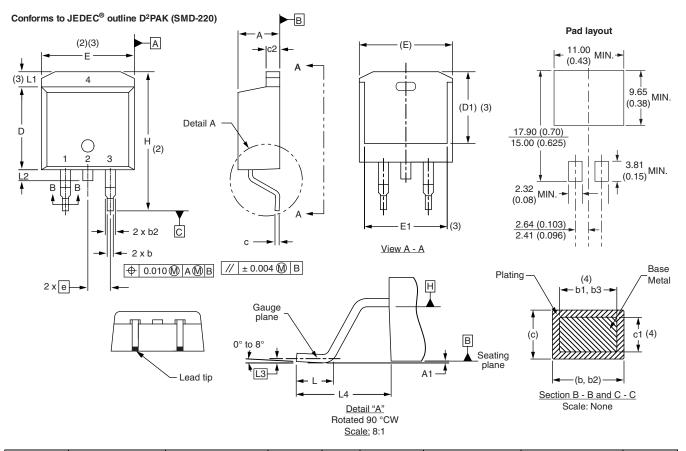


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D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches

SHA



SYMBOL	MILLIM	ETERS	INC	HES	NOTES	SYMBOL	MILLIM	IETERS	INC	INCHES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	е	2.54	BSC	0.100	) BSC	
b2	1.14	1.78	0.045	0.070		Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25	BSC	0.010	) BSC	
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-263AB

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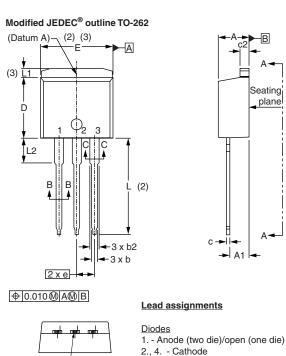
### **Outline Dimensions**



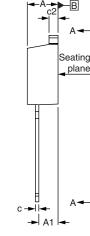
**Vishay Semiconductors** 

**TO-262** 

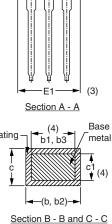
#### **DIMENSIONS** in millimeters and inches



Lead tip -



E1 Plating



Е

D1(3)

Scale: None

SYMBOL	MILLIM	ETERS	INC	INCHES			
STNIBUL	MIN.	MAX.	MIN.	MAX.	NOTES		
А	4.06	4.83	0.160	0.190			
A1	2.03	3.02	0.080	0.119			
b	0.51	0.99	0.020	0.039			
b1	0.51	0.89	0.020	0.035	4		
b2	1.14	1.78	0.045	0.070			
b3	1.14	1.73	0.045	0.068	4		
С	0.38	0.74	0.015	0.029			
c1	0.38	0.58	0.015	0.023	4		
c2	1.14	1.65	0.045	0.065			
D	8.51	9.65	0.335	0.380	2		
D1	6.86	8.00	0.270	0.315	3		
E	9.65	10.67	0.380	0.420	2, 3		
E1	7.90	8.80	0.311	0.346	3		
е	2.54	2.54 BSC		) BSC			
L	13.46	14.10	0.530	0.555			
L1	-	1.65	-	0.065	3		
L2	3.36	3.71	0.132	0.146			

3. - Anode

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

(5) Controlling dimension: inches (6)

<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body <sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum), D1 (minimum) and L2 where dimensions derived the actual package outline

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